

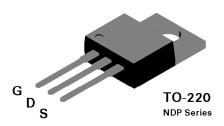
NDP6060 / NDB6060 N-Channel Enhancement Mode Field Effect Transistor

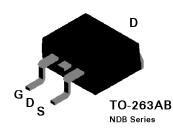
General Description

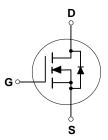
These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulses in the avalanche and commutation modes. These devices are particularly suited for low voltage applications such as automotive, DC/DC converters, PWM motor controls, and other battery powered circuits where fast switching, low in-line power loss, and resistance to transients are needed.

Features

- 48A, 60V. $R_{DS(ON)} = 0.025\Omega$ @ $V_{GS} = 10V$.
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- 175°C maximum junction temperature rating.
- High density cell design for extremely low R_{DS(ON)}.
- TO-220 and TO-263 (D²PAK) package for both through hole and surface mount applications.







Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

| Symbol | Parameter | NDP6060 | NDB6060 | Units | | |
|-------------------|---|------------|---------|-------|--|--|
| V _{DSS} | Drain-Source Voltage | 60 | | | | |
| V_{DGR} | Drain-Gate Voltage ($R_{GS} \le 1 \text{ M}\Omega$) | 60 | | | | |
| V _{GSS} | Gate-Source Voltage - Continuous | ±20 | | | | |
| | - Nonrepetitive (t _p < 50 μs) | ± 40 | | | | |
| I _D | Drain Current - Continuous T _c =25°C | 48 | | | | |
| | - Continuous T _c =100°C | 32 144 | | | | |
| | - Pulsed | | | | | |
| P _D | Total Power Dissipation @ T _c = 25°C | 10 | 00 | W | | |
| | Derate above 25°C | 0. | W/°C | | | |
| T_J , T_{STG} | Operating and Storage Temperature Range | -65 to 175 | | | | |
| T _L | Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds | 2 | 75 | °C | | |

| Symbol | Parameter | Conditions | | | Тур | Max | Units |
|---------------------------------|---|---|------------------------|-------|------|-------|-------|
| DRAIN-SC | DURCE AVALANCHE RATINGS (Note 1) | | | | | | |
| W _{DSS} | Single Pulse Drain-Source Avalanche Energy | $V_{DD} = 25 \text{ V}, I_{D} = 48 \text{ A}$ | | | | 200 | mJ |
| I _{AR} | Maximum Drain-Source Avalanche Cur | rent | | | 48 | Α | |
| OFF CHA | RACTERISTICS | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$ | 60 | | | V | |
| I _{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$ | | | | 250 | μΑ |
| | | | T _J = 125°C | | | 1 | mA |
| I _{GSSF} | Gate - Body Leakage, Forward | $V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$ | • | | | 100 | nA |
| GSSR | Gate - Body Leakage, Reverse | $V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$ | | | | -100 | nA |
| ON CHAR | RACTERISTICS (Note 1) | | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$ | | 2 | 2.9 | 4 | V |
| | | | T _J = 125°C | 1.4 | 2.3 | 3.6 | |
| $R_{\scriptscriptstyle DS(ON)}$ | Static Drain-Source On-Resistance | $V_{GS} = 10 \text{ V}, I_{D} = 24 \text{ A}$ | · | | 0.02 | 0.025 | Ω |
| | | | | 0.032 | 0.04 | | |
| I _{D(on)} | On-State Drain Current | $V_{GS} = 10 \text{ V}, V_{DS} = 10 \text{ V}$ | | 48 | | | Α |
| g _{FS} | Forward Transconductance | $V_{DS} = 10 \text{ V}, I_{D} = 24 \text{ A}$ | | 10 | 19 | | S |
| DYNAMIC | CHARACTERISTICS | | | | | | |
| C _{iss} | Input Capacitance | $V_{DS} = 25 \text{ V}, \ V_{GS} = 0 \text{ V},$ | | | 1190 | 1800 | pF |
| C _{oss} | Output Capacitance | f = 1.0 MHz | | | 475 | 800 | pF |
| C _{rss} | Reverse Transfer Capacitance | | | | 150 | 400 | pF |
| SWITCHII | NG CHARACTERISTICS (Note 1) | | | | | | |
| t _{D(on)} | Turn - On Delay Time | $V_{DD} = 30 \text{ V}, I_{D} = 48 \text{ A},$ | | 10 | 20 | nS | |
| ţ | Tum - On Rise Time | V_{GS} = 10 V, R_{GEN} = 7.5 Ω | | 145 | 300 | nS | |
| t _{D(off)} | Turn - Off Delay Time | 1 | | | 28 | 60 | nS |
| ţ, | Turn - Off Fall Time | | | | 77 | 150 | nS |
| Q_g | Total Gate Charge | $V_{DS} = 48 \text{ V},$ | | | 39 | 70 | nC |
| Q_{gs} | Gate-Source Charge | $V_{DS} = 48 \text{ V},$ $I_{D} = 48 \text{ A}, V_{GS} = 10 \text{ V}$ | | | 7.6 | | nC |
| Q_{gd} | Gate-Drain Charge | | | | 22 | | nC |

| Symbol | Parameter | Conditions | Conditions | | | | Units |
|------------------|--|---|------------------------|------|------|-----|-------|
| DRAIN-S | OURCE DIODE CHARACTERISTICS | • | | | | | |
| l _s | Maximum Continuos Drain-Source Diode | | | | 48 | Α | |
| I _{SM} | Maximum Pulsed Drain-Source Diode Fo | | | 144 | Α | | |
| V _{SD} | Drain-Source Diode Forward Voltage | $V_{GS} = 0 \text{ V}, I_{S} = 24 \text{ A (Note 1)}$ | | | 0.9 | 1.3 | V |
| | | | T _J = 125°C | | 8.0 | 1.2 | • |
| t _{rr} | Reverse Recovery Time | $V_{GS} = 0 \text{ V}, I_F = 48 \text{ A},$ | | 35 | 87 | 140 | ns |
| I _{rr} | Reverse Recovery Current | $dl_{F}/dt = 100 \text{ A/}\mu\text{s}$ | | 2 | 3.6 | 8 | Α |
| THERMA | L CHARACTERISTICS | <u>.</u> | | | | • | |
| R _{øJC} | Thermal Resistance, Junction-to-Case | | | 1.5 | °C/W | | |
| R _{eJA} | Thermal Resistance, Junction-to-Ambier | | | 62.5 | °C/W | | |

Note: 1. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.

Typical Electrical Characteristics

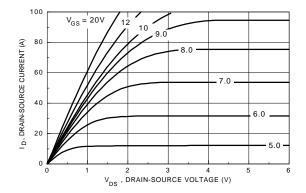


Figure 1. On-Region Characteristics

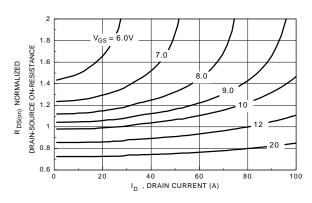


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

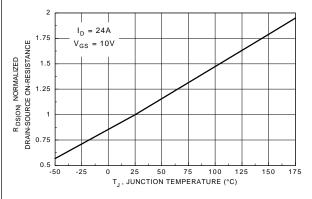


Figure 3. On-Resistance Variation with Temperature

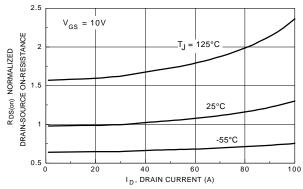


Figure 4. On-Resistance Variation with Drain Current and Temperature

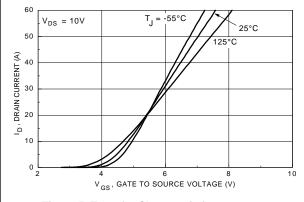


Figure 5. Transfer Characteristics

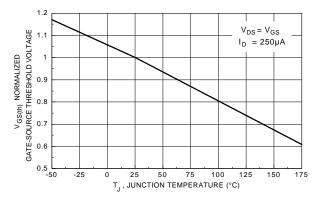


Figure 6. Gate Threshold Variation with Temperature

Typical Electrical Characteristics (continued)

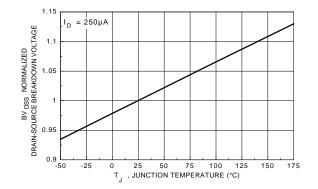


Figure 7. Breakdown Voltage Variation with Temperature

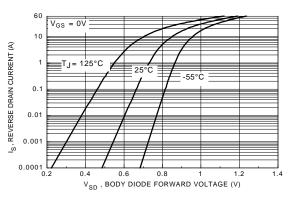


Figure 8. Body Diode Forward Voltage Variation with Current and Temperature

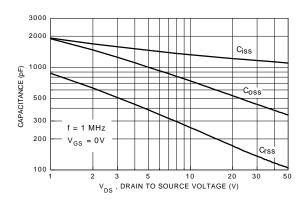


Figure 9. Capacitance Characteristics

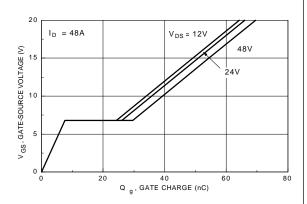


Figure 10. Gate Charge Characteristics

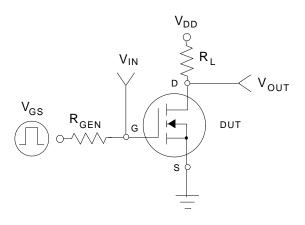


Figure 11. Switching Test Circuit

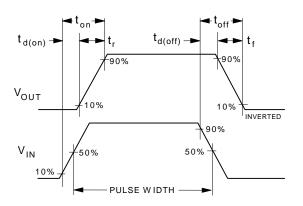
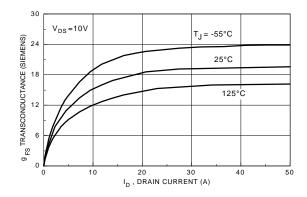


Figure 12. Switching Waveforms

Typical Electrical Characteristics (continued)



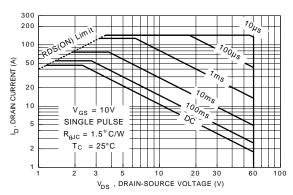


Figure 13. Transconductance Variation with Drain Current and Temperature

Figure 14. Maximum Safe Operating Area

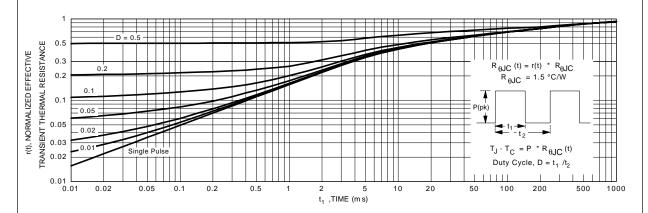
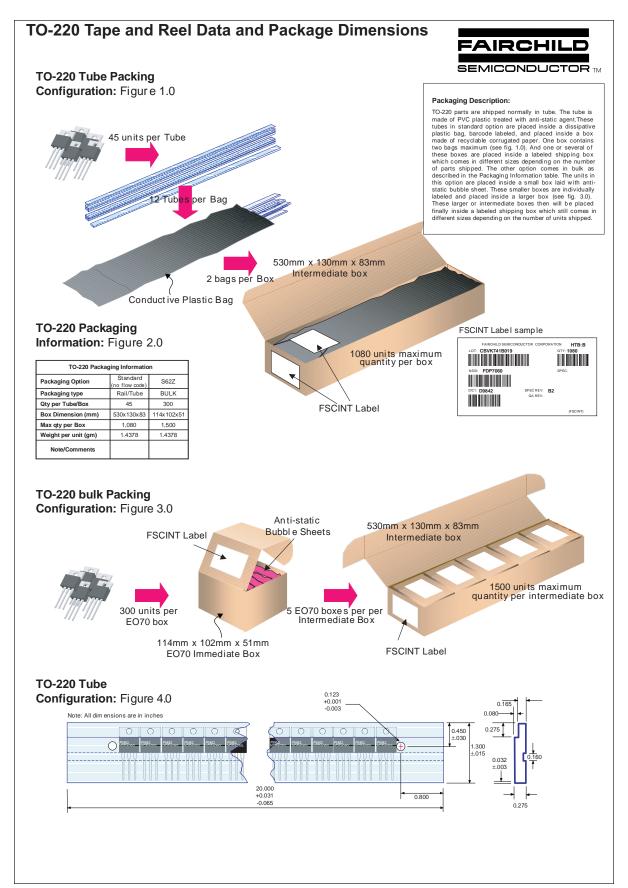
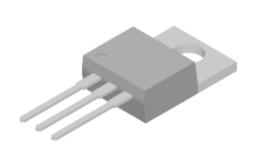


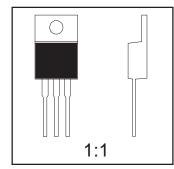
Figure 15. Transient Thermal Response Curve



TO-220 Tape and Reel Data and Package Dimensions, continued

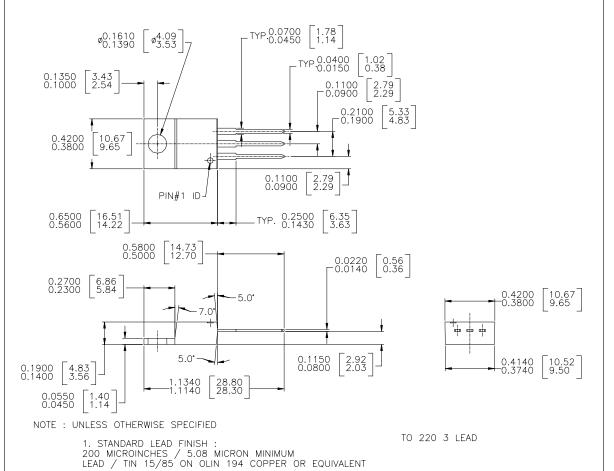
TO-220 (FS PKG Code 37)

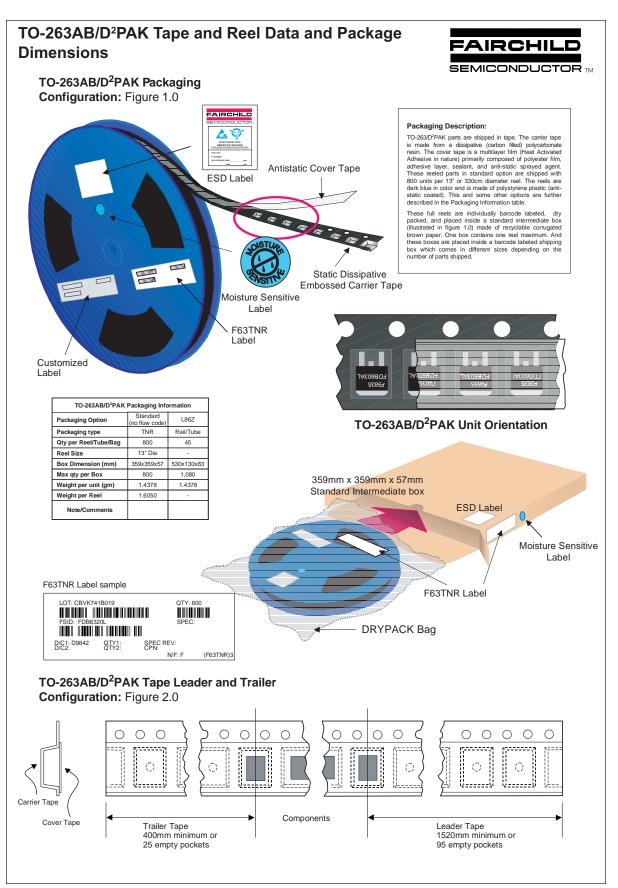




Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

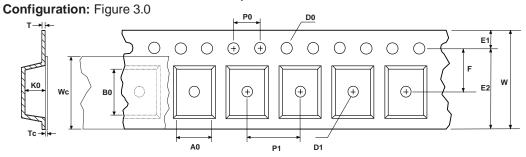
Part Weight per unit (gram): 1.4378





TO-263AB/D²PAK Tape and Reel Data and Package Dimensions, continued

TO-263AB/D²PAK Embossed Carrier Tape



User Direction of Feed

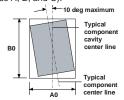
| Dimensions are in millimeter | | | | | | | | | | | | | | |
|--|------------------|------------------|----------------|-----------------|-----------------|-----------------|--------------|------------------|----------------|---------------|-----------------|-------------------|----------------|-----------------|
| Pkg type | Α0 | В0 | w | D0 | D1 | E1 | E2 | F | P1 | P0 | K0 | Т | Wc | Тс |
| TO263AB/ D ² PAK (24mm) | 10.60 +/-0.10 | 15.80 +/-0.10 | 24.0 +/-0.3 | 1.55 +/-0.05 | 1.60 +/-0.10 | 1.75 +/-0.10 | 22.25 min | 11.50 +/-0.10 | 16.0 +/-0.1 | 4.0 +/-0.1 | 4.90 +/-0.10 | 0.450 +/-0.150 | 21.0 +/-0.3 | 0.06 +/-0.02 |

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)

Component Rotation

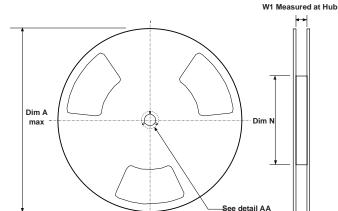


Sketch B (Top View)
Component Rotation

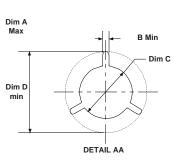


Sketch C (Top View)
Component lateral movement

TO-263AB/D²PAK Reel Configuration: Figure 4.0



13" Diameter Option



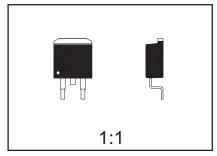
W2 max Measured at Hub

| Dimensions are in inches and millimeters | | | | | | | | | |
|--|----------------|--------------|--------------|-----------------------------------|---------------|-------------|----------------------------------|---------------|--------------------------------|
| Tape Size | Reel Option | Dim A | Dim B | Dim C | Dim D | Dim N | Dim W1 | Dim W2 | Dim W3 (LSL-USL) |
| 24mm | 13" Dia | 13.00 330 | 0.059 1.5 | 512 +0.020/-0.008 13 +0.5/-0.2 | 0.795 20.2 | 4.00 100 | 0.961 +0.078/-0.000 24.4 +2/0 | 1.197 30.4 | 0.941 - 0.1.079 23.9 - 27.4 |

TO-263AB/D²PAK Tape and Reel Data and Package Dimensions, continued

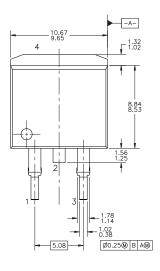
TO-263AB/D²PAK (FS PKG Code 45)

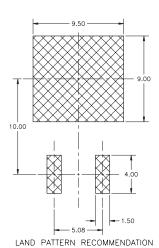


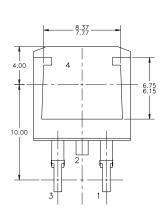


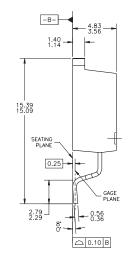
Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 1.4378









- NOTES: UNLESS OTHERWISE SPECIFIED

 A) ALL DIMENSIONS ARE IN MILLIMETERS.
 B) STANDARD LEAD FINISH:
 200 MICROINCHES / 5.08 MICROMETERS MIN.
 LEAD/TIN 15/85 ON OLIN 194 COPPER OR
 EQUIVALENT.
 C) MAXIMUM YERTICAL BURR ON HEATSINK NOT
 TO EXCEED 0.003 INCH / 0.05mm.
 D) NO PACKAGE CHIPS, CRACKS OR SURFACE
 IDENTIFICATION ALLOWED AFTER FORMING.
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